

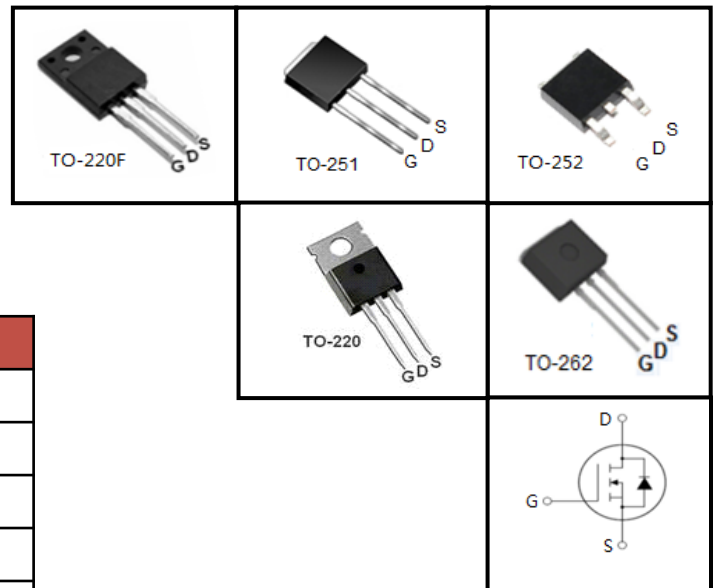
600V N-Channel MOSFET

FEATURES

- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)



Device Marking and Package Information		
Device	Package	Marking
HF2N60	TO-220F	HF2N60
HP2N60	TO-220	HP2N60
HU2N60	TO-251	HU2N60
HD2N60	TO-252	HD2N60
HB2N60	TO-262	HB2N60

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, unless otherwise noted							
Parameter	Symbol	Value					Unit
		TO-220F	TO-262	TO-220	TO-251	TO-252	
Drain-Source Voltage ($V_{GS} = 0\text{V}$)	V_{DSS}	600					V
Continuous Drain Current	I_D	2					A
Pulsed Drain Current (note1)	I_{DM}	8					A
Gate-Source Voltage	V_{GSS}	± 30					V
Single Pulse Avalanche Energy (note2)	E_{AS}	28.8					mJ
Avalanche Current (note1)	I_{AS}	2.4					A
Repetitive Avalanche Energy (note1)	E_{AR}	17.28					mJ
Power Dissipation ($T_C = 25^\circ\text{C}$)	P_D	20		25		W	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55~+150					$^\circ\text{C}$

Thermal Resistance							
Parameter	Symbol	Value					Unit
		TO-220F	TO-262	TO-251	TO-252	TO-220	
Thermal Resistance, Junction-to-Case	R_{thJC}	6.25		5			$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient	R_{thJA}	62.5		60			

Specifications $T_J = 25^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	600	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 600V, V_{GS} = 0V, T_J = 25^\circ\text{C}$	--	--	1	μA
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 30V$	--	--	± 100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	3.0	--	4.0	V
Drain-Source On-Resistance (Note3)	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 1.0A$	--	3.5	4.2	Ω
Dynamic						
Input Capacitance	C_{iss}	$V_{GS} = 0V,$ $V_{DS} = 25V,$ $f = 1.0\text{MHz}$	--	249.5	--	pF
Output Capacitance	C_{oss}		--	30	--	
Reverse Transfer Capacitance	C_{rss}		--	4.2	--	
Total Gate Charge	Q_g	$V_{DD} = 480V, I_D = 2.0A,$ $V_{GS} = 10V$	--	11	--	nC
Gate-Source Charge	Q_{gs}		--	1.55	--	
Gate-Drain Charge	Q_{gd}		--	6.15	--	
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 300V, I_D = 2.0A,$ $R_G = 25\Omega$	--	33.6	--	ns
Turn-on Rise Time	t_r		--	7.2	--	
Turn-off Delay Time	$t_{d(off)}$		--	64	--	
Turn-off Fall Time	t_f		--	31.2	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I_S	$T_C = 25^\circ\text{C}$	--	--	2	A
Pulsed Diode Forward Current	I_{SM}		--	--	8	
Body Diode Voltage	V_{SD}	$T_J = 25^\circ\text{C}, I_{SD} = 1.0A, V_{GS} = 0V$	--	--	1.4	V
Reverse Recovery Time	t_{rr}	$V_{GS} = 0V, I_S = 2.0A,$ $di_F/dt = 100A/\mu s$	--	490	--	ns
Reverse Recovery Charge	Q_{rr}		--	0.6	--	μC

Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. $L = 10.0\text{mH}, V_{DD} = 50V, R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$
3. Pulse Test: Pulse width $\leq 300\mu s$, Duty Cycle $\leq 1\%$

Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics ($T_J = 25^\circ\text{C}$)

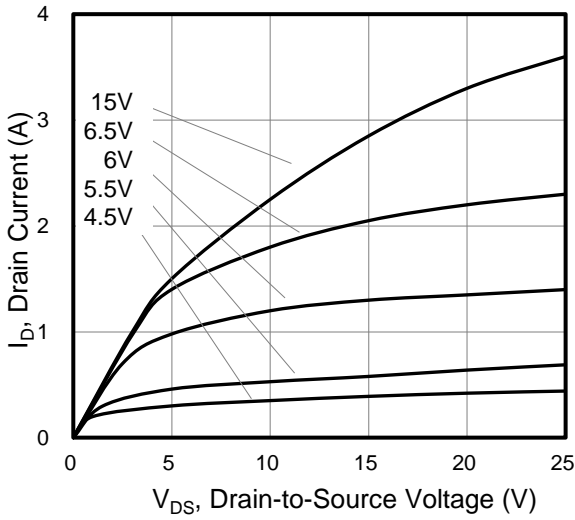


Figure 2. Body Diode Forward Voltage

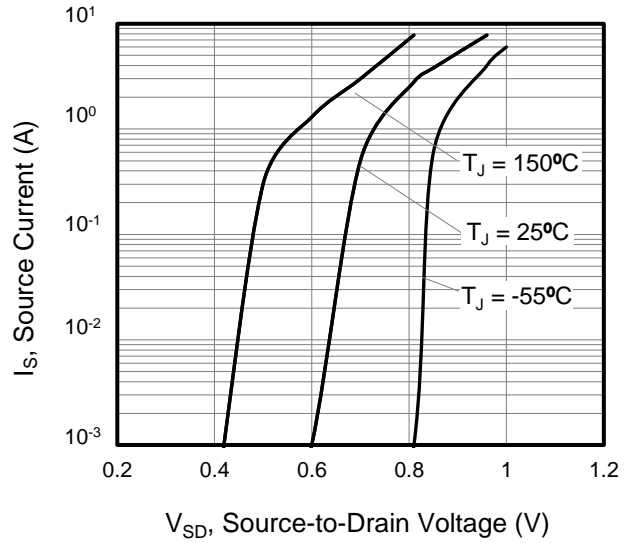


Figure 3. Drain Current vs. Temperature

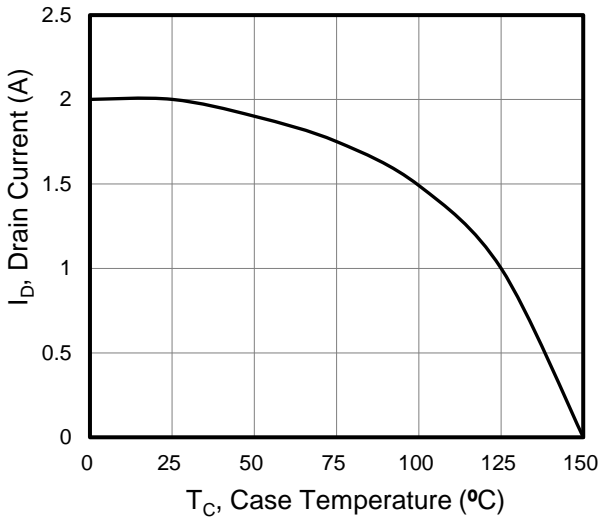


Figure 4. Power Dissipation vs. Temperature TO-251,TO-252

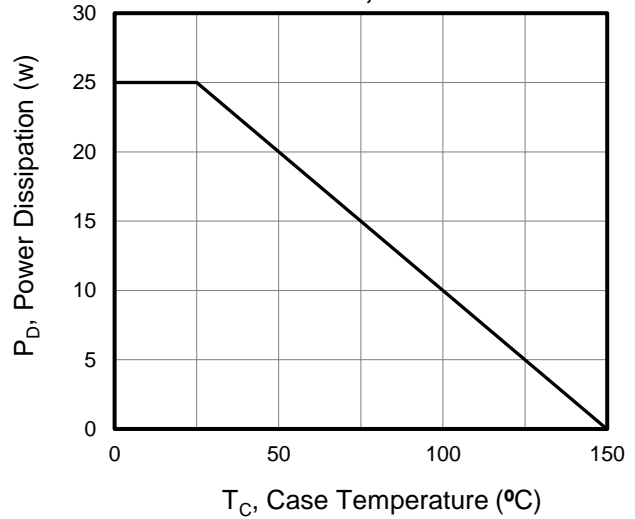


Figure 5. Transfer Characteristics

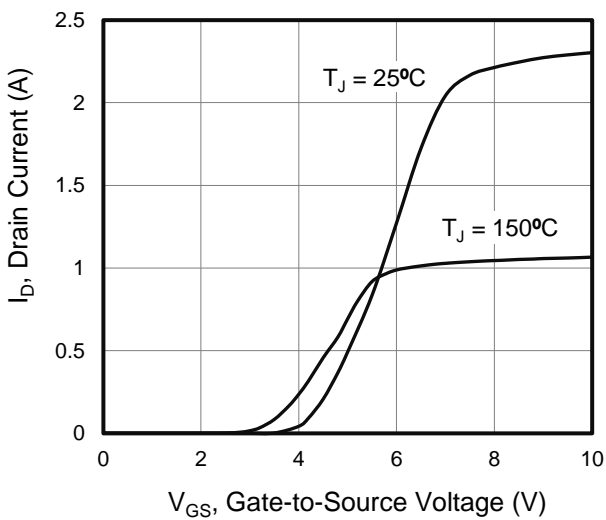
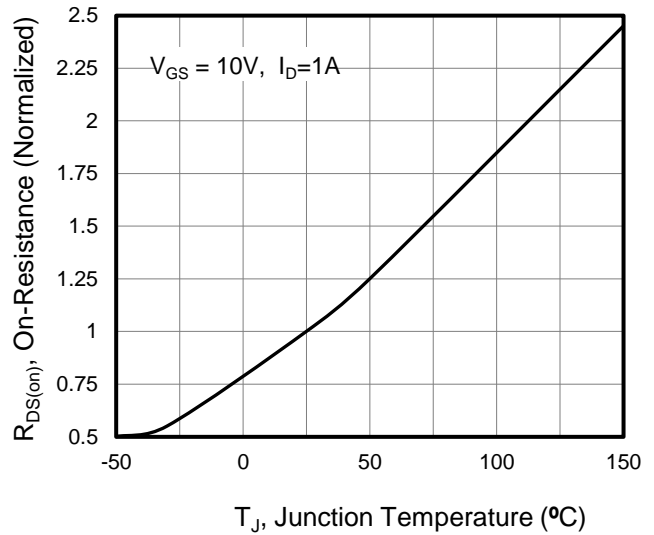


Figure 6. On-Resistance vs. Temperature



Typical Characteristics $T_j = 25^\circ\text{C}$, unless otherwise noted

Figure 7. Capacitance

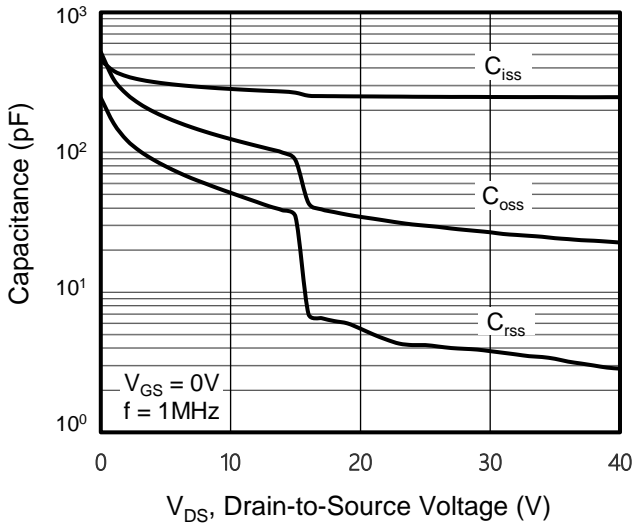


Figure 8. Gate Charge

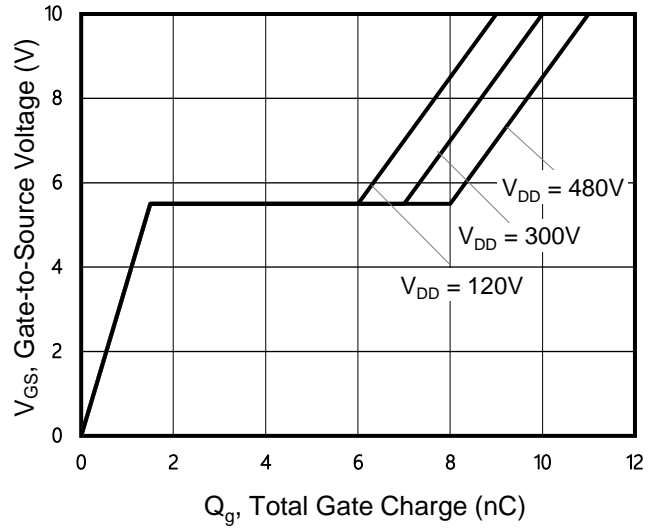


Figure 9. Transient Thermal Impedance TO-251,TO-252,TO-220

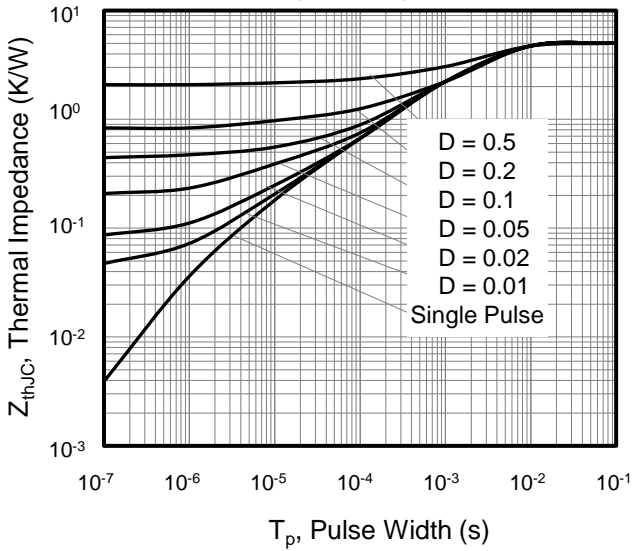


Figure 10. Transient Thermal Impedance TO-220F,TO-126F

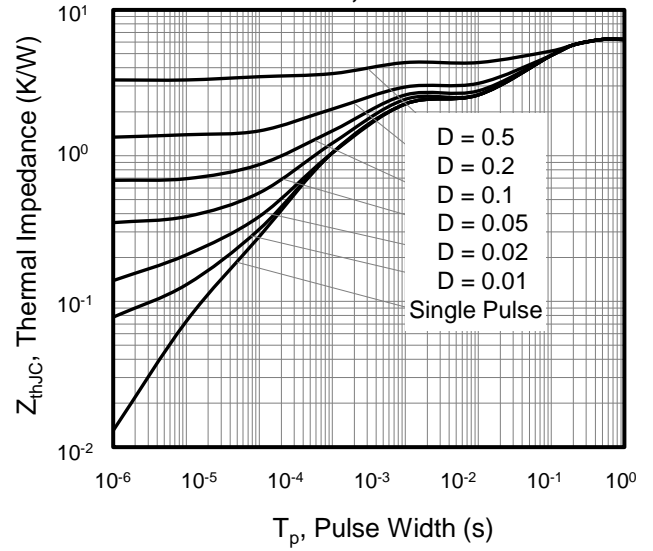


Figure A: Gate Charge Test Circuit and Waveform

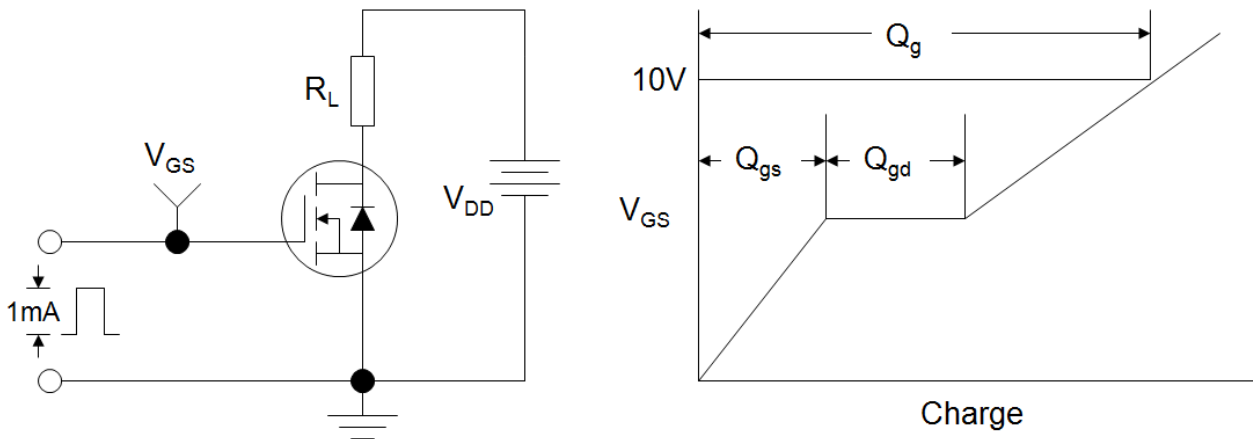


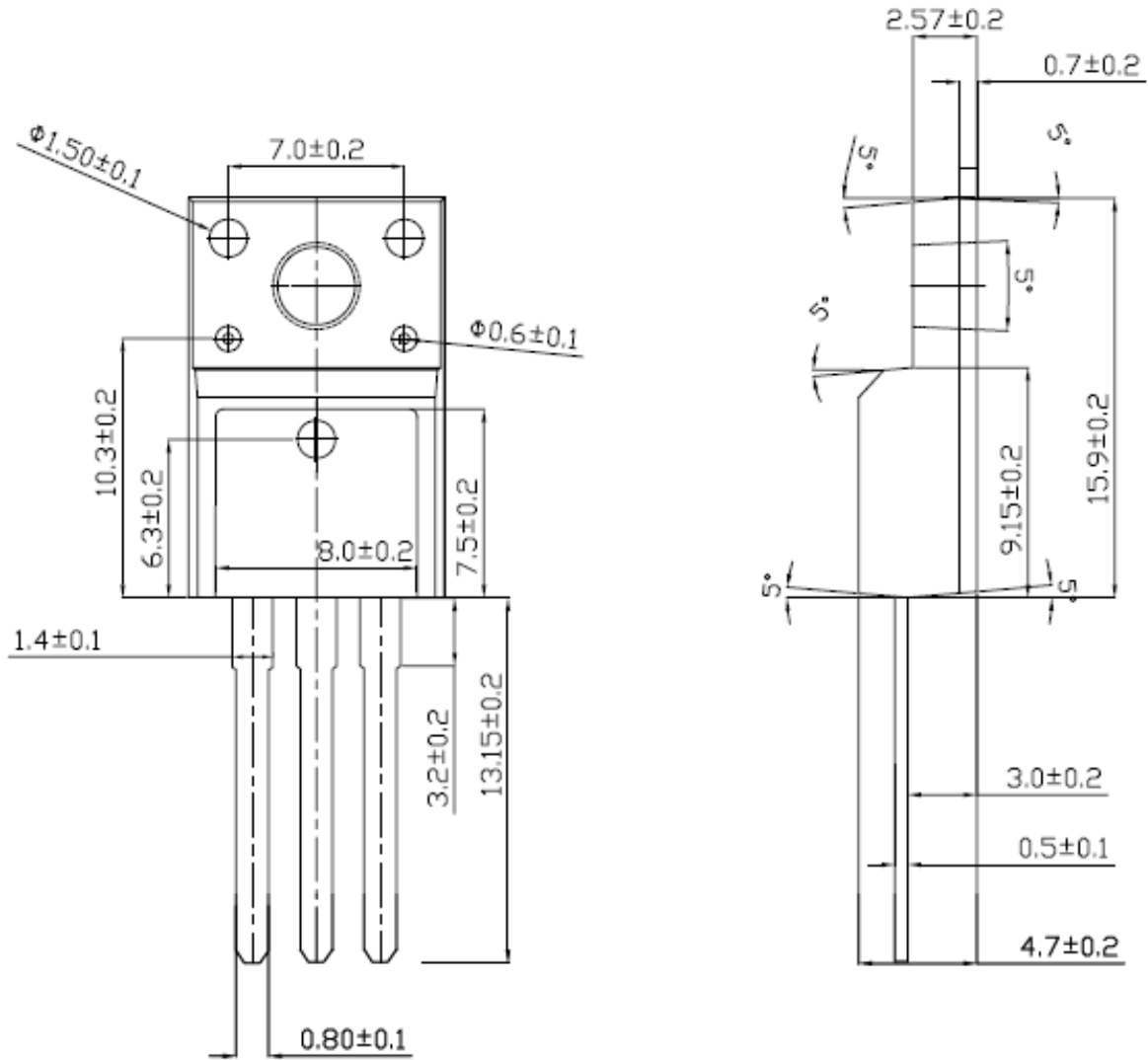
Figure B: Resistive Switching Test Circuit and Waveform



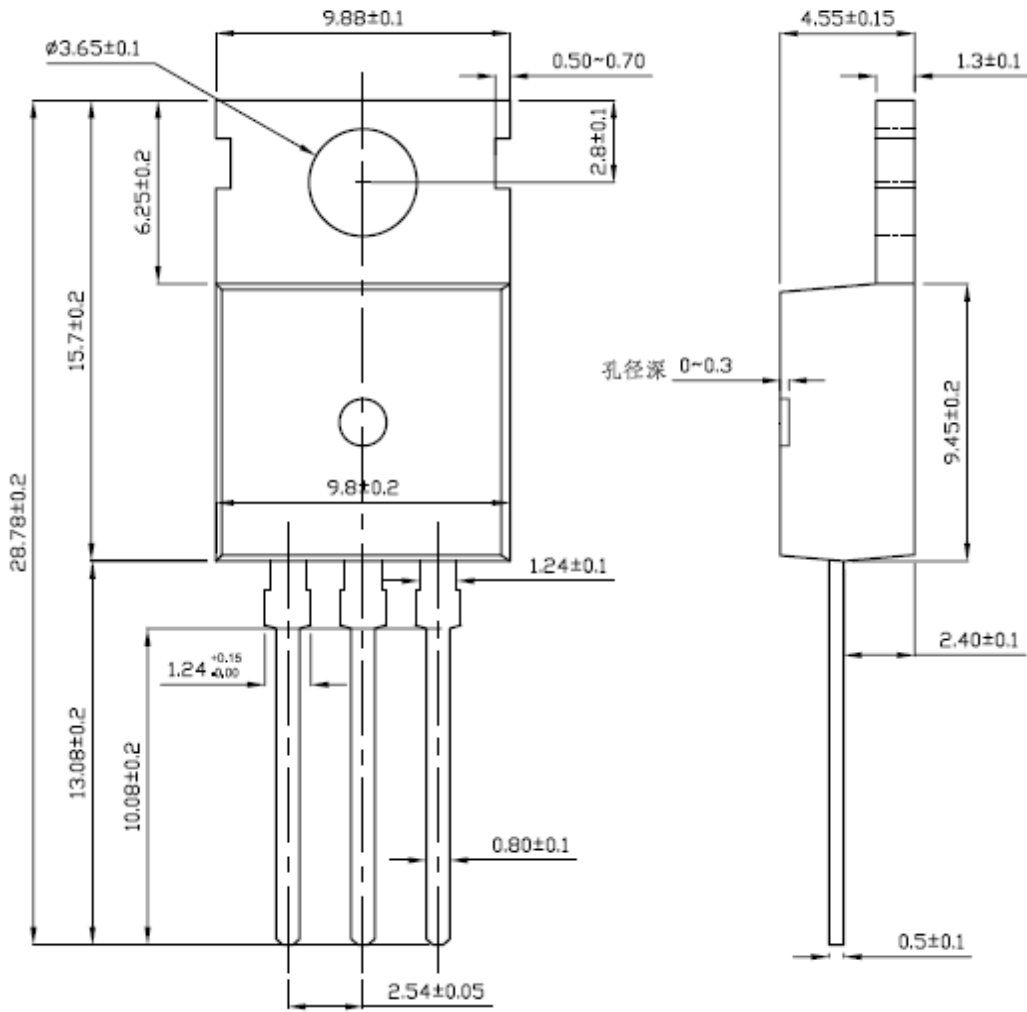
Figure C: Unclamped Inductive Switching Test Circuit and Waveform



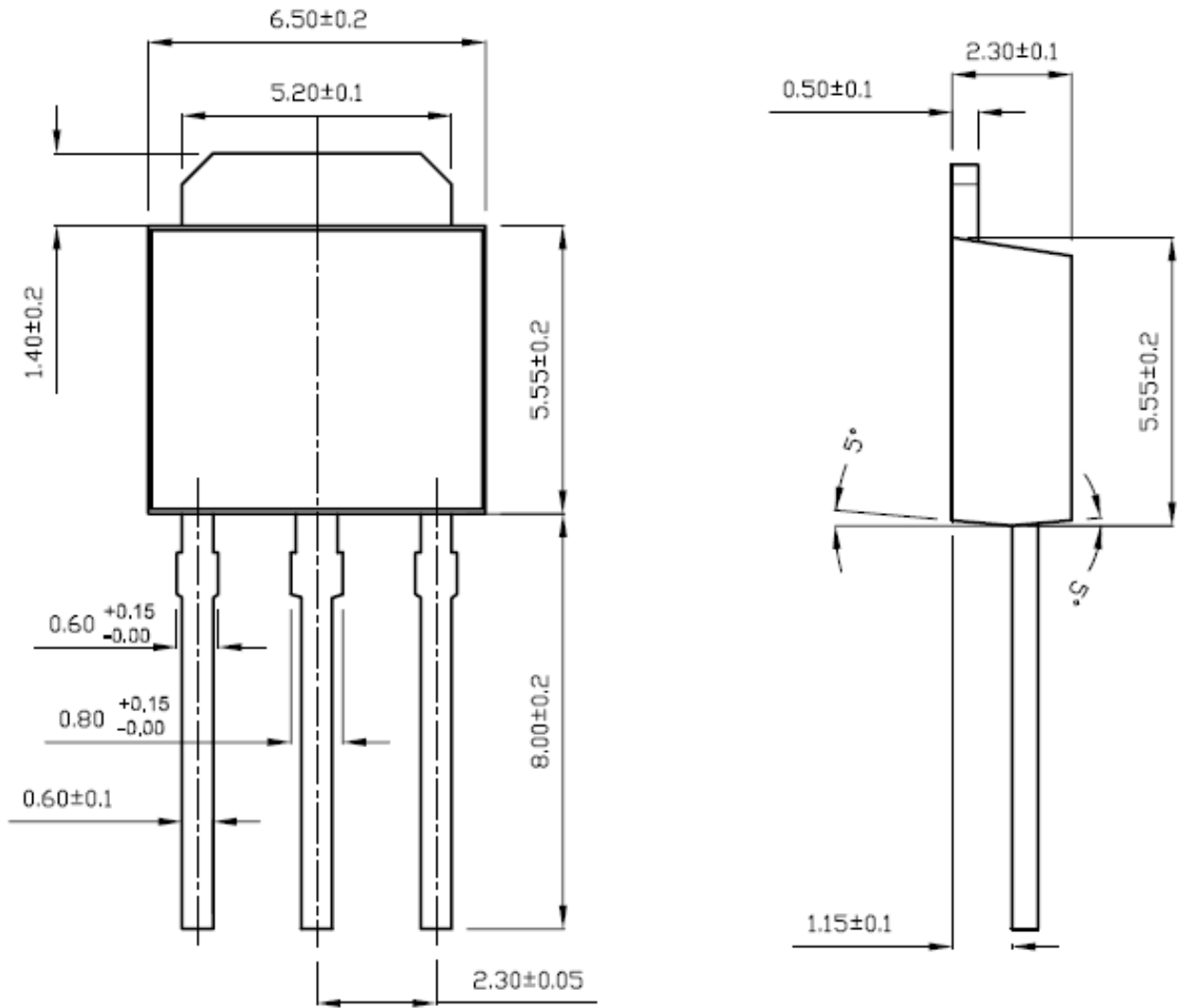
TO-220F



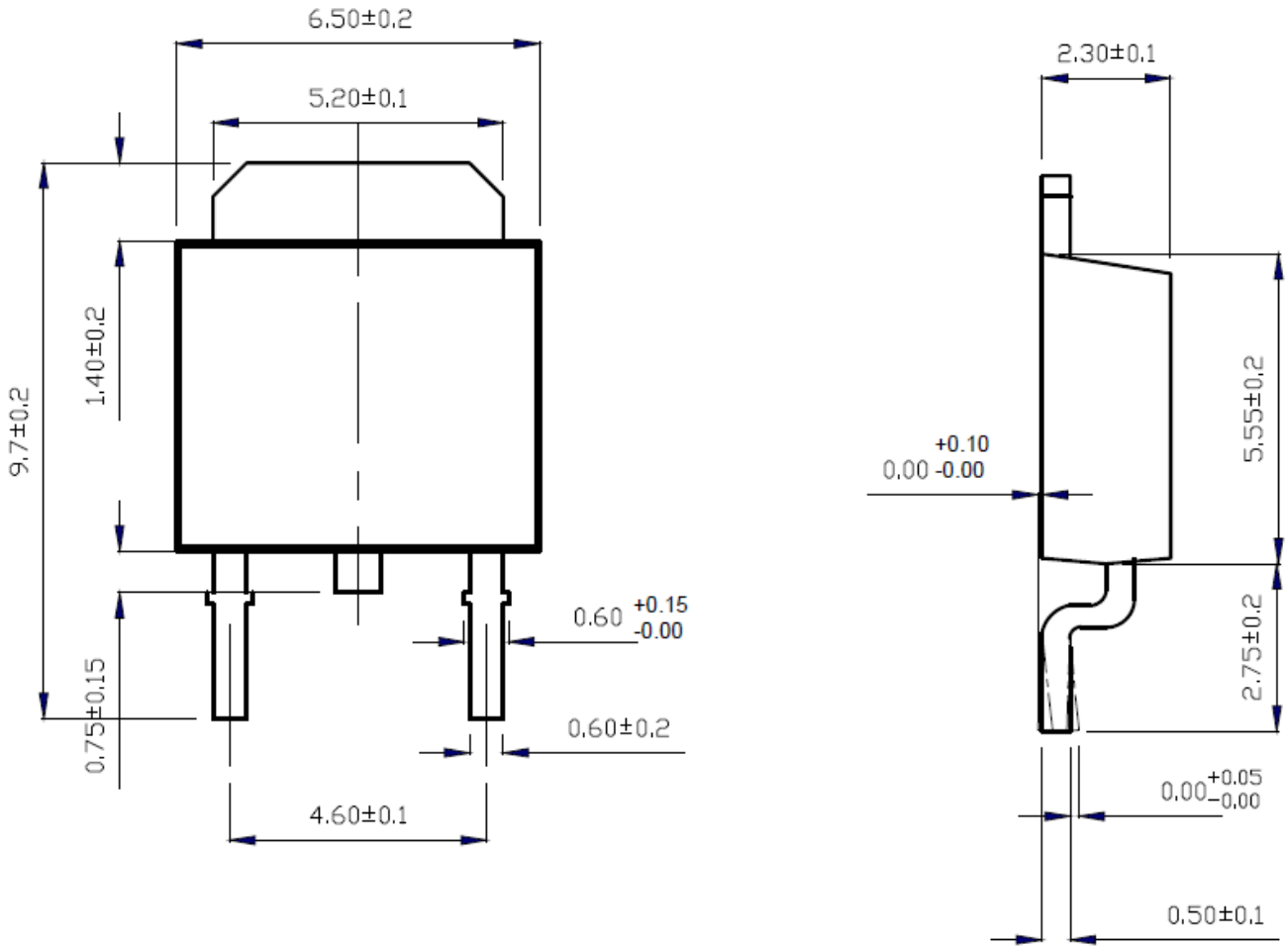
TO-220



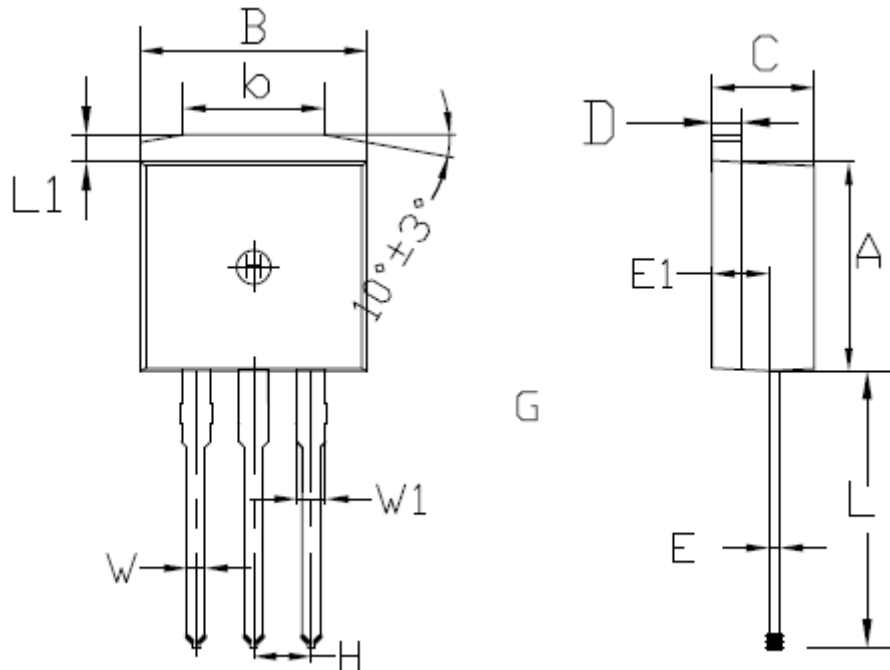
TO-251



TO-252



TO-262



SYMBOLS	MILLIMETERS	
	MIN	MAX
A	8.80	9.30
B	9.70	10.30
C	4.25	4.75
D	1.20	1.45
E	0.40	0.60
L	12.25	13.75
L1	1.15	1.45
E1	2.40	2.60
W	0.80	0.82
W1	1.20	1.30
H	2.54TYP	
b	5.50	6.50

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